



In re Application of
Katsuhide MANABE et al.

Serial No.: 10/052,347

Group Art Unit: 2812

Filed: January 23, 2002

Examiner: Mulpuri, S.

For: A METHOD FOR MANUFACTURING A GALLIUM NITRIDE GROUP COMPOUND SEMICONDUCTOR

Honorable Commissioner of Patents
Washington, DC 20231

STATEMENT OF SUBSTANCE OF INTERVIEW

Sir:

Applicant provides herewith his Statement of Substance of the personal interview which was conducted on April 12, 2004.

Specifically, Applicant states that during the interview, the Examiner and Applicant's undersigned representative, discussed claims 19-36 and 119-121. Applicant pointed out that the Sayyah references ("A Study of Growth Mechanisms and Electrical and Optical Properties of Epitaxial $\text{Al}_x\text{Ga}_{1-x}\text{N}$ Layers Grown by Atmospheric Pressure Metalorganic Chemical Vapor Deposition", A Dissertation Presented to the Faculty of the Graduate School, University of Southern California, February 1986) does not teach or suggest the claimed invention.

Specifically, Applicant's undersigned representative pointed out to the Examiner that Sayyah does not teach or suggest a method which includes setting a mixing ratio of a silicon-containing gas to at least one other raw material gas at a desired value in a range over which a conductivity (e.g., carrier concentration) of the gallium nitride group compound semiconductor increases substantially proportionally with the mixing ratio.

The Examiner stated that she would consider the arguments of Applicant's undersigned representative.

Respectfully Submitted,

Date: 5/10/04



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